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Notice of Allowability	Application No.	Applicant(s)	
	09/977,375	ONO ET AL.	
	Examiner	Art Unit	
	Junghwa M. Im	2811	
The MAILING DATE of this communication appeal claims being allowable, PROSECUTION ON THE MERITS IS herewith (or previously mailed), a Notice of Allowance (PTOL-85) NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT R of the Office or upon petition by the applicant. See 37 CFR 1.313	(OR REMAINS) CLOSED in or other appropriate communication is selected and MPEP 1308.	n this application. If not including the unication will be mailed in de	uded ue course. THIS
2. ☑ The allowed claim(s) is/are <u>1,2,5-11,14 and 15</u> .			
3. Acknowledgment is made of a claim for foreign priority una Mall b) Some* c) None of the: 1. Certified copies of the priority documents have 2. Certified copies of the priority documents have 3. Copies of the certified copies of the priority do International Bureau (PCT Rule 17.2(a)). * Certified copies not received: Applicant has THREE MONTHS FROM THE "MAILING DATE" noted below. Failure to timely comply will result in ABANDONN THIS THREE-MONTH PERIOD IS NOT EXTENDABLE. 4. A SUBSTITUTE OATH OR DECLARATION must be subm INFORMAL PATENT APPLICATION (PTO-152) which give 5. CORRECTED DRAWINGS (as "replacement sheets") must (a) including changes required by the Notice of Draftspers 1) hereto or 2) to Paper No./Mail Date (b) including changes required by the attached Examiner' Paper No./Mail Date Identifying indicia such as the application number (see 37 CFR 1 each sheet. Replacement sheet(s) should be labeled as such in the deponsion of the de	e been received. e been received in Application cuments have been received of this communication to file MENT of this application. Initted. Note the attached EXA es reason(s) why the oath of the submitted. Inited Son's Patent Drawing Review of Samendment / Comment of the header according to 37 CF asit of BIOLOGICAL MATING.	on No d in this national stage appliance a reply complying with the AMINER'S AMENDMENT or declaration is deficient. W (PTO-948) attached r in the Office action of the drawings in the front (not FR 1.121(d).	requirements r NOTICE OF
Attachment(s) 1. ☐ Notice of References Cited (PTO-892) 2. ☐ Notice of Draftperson's Patent Drawing Review (PTO-948) 3. ☐ Information Disclosure Statements (PTO-1449 or PTO/SB/0 Paper No./Mail Date 4. ☐ Examiner's Comment Regarding Requirement for Deposit of Biological Material	6. ☐ Interview S Paper No. 08), 7. ☒ Examiner's	oformal Patent Application (Formal Patent Application (Formal Patent) (PTO-413), //Mail Date Amendment/Comment Statement of Reasons for A	·

SUPERVISORY PATENT EXAMINER
TECHNOLOGY CENTER 2800

Application/Control Number: 09/977,375

Art Unit: 2811

DETAILED ACTION

EXAMINER'S AMENDMENT

An examiner's amendment to the record appears below. Should the changes and/or additions be unacceptable to applicant, an amendment may be filed as provided by 37 CFR 1.312. To ensure consideration of such an amendment, it MUST be submitted no later than the payment of the issue fee.

The application has been amended as follows.

Cancel claims 12 and 13.

Allowable Subject Matter

Claims 1-2, 5-11 and 14-15 are allowed.

The following is an examiner's statement of reasons for allowance.

Prior art fails to teach or render obvious singularly or with combinations of elements as set forth in the claims, in particular, a 3-5 group compound semiconductor device comprising a GaAs substrate, a buffer layer on the GaAs substrate and an epitaxial crystal layer on the buffer layer, and the layers formed by an epitaxial crystal growth wherein the buffer layer and the epitaxial crystal layer on the buffer layer are 3-5 group compound semiconductors each independently represented by the general formula $In_xGa_yAl_zAs$ (wherein, $0 \le x \le 1$, $0 \le y \le 1$, $0 \le z \le 1$, x + y + z = 1), and the buffer layer being laminated with n times $(1 \le n \le 30)$ of $Ga_{1-z}Al_zAs$ (wherein, $0 < z \le 1$) layer and GaAs layer and the dislocation density in the epitaxial crystal layer being $2000/cm^2$ or less, or the dislocation density in the epitaxial crystal layer on the buffer layer being 1/3 or less of the dislocation density in the GaAs substrate.

Application/Control Number: 09/977,375

Art Unit: 2811

Page 3

Any comments considered necessary by applicant must be submitted no later than the payment of the issue fee and, to avoid processing delays, should preferably accompany the issue fee. Such submissions should be clearly labeled "Comments on Statement of Reasons for

Allowance."

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Junghwa M. Im whose telephone number is (571) 272-1655. The examiner can normally be reached on MON.-FRI. 8:30AM-5:00PM.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Eddie C. Lee can be reached on (571) 272-1732. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

jmi

EDDIE LEE SUPERVISORY PATENT EXAMINER

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